TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1313

Audio Frequency Low Power Amplifier Applications Driver Stage Amplifier Applications Switching Applications

• Excellent hFE linearity: hFE (2) = 25 (min) $at\ V_{CE} = -6\ V,\ I_{C} = -400\ mA$

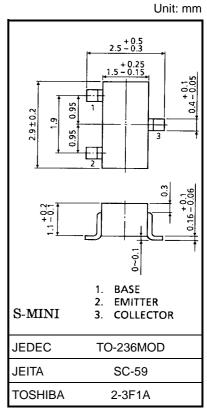
• High voltage: $V_{CEO} = -50 \text{ V (min)}$

• Complementary to 2SC3325

• Small package

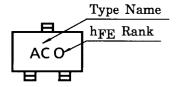
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	IC	-500	mA
Base current	Ι _Β	-50	mA
Collector power dissipation	P _C	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C



Weight: 0.012 g (typ.)

Marking



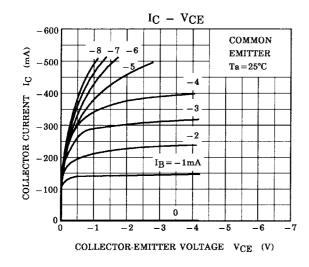


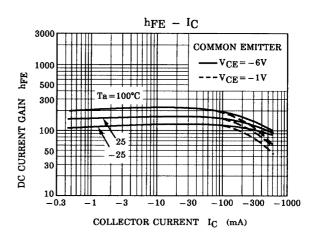
Electrical Characteristics (Ta = 25°C)

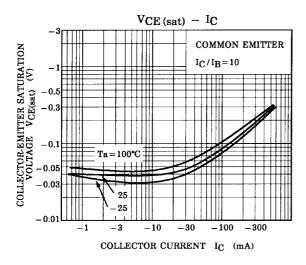
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-0.1	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	μΑ
DC current gain	h _{FE (1)} (Note)	V _{CE} = -1 V, I _C = -100 mA	70	_	240	
	h _{FE (2)} (Note)	V _{CE} = -6 V, I _C = -400 mA	25	_	_	
Collector-emitter saturation voltage	V _{CE} (sat)	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$	_	-0.1	-0.25	V
Base-emitter voltage	V _{BE}	$V_{CE} = -1 \text{ V, } I_{C} = -100 \text{ mA}$	_	-0.8	-1.0	V
Transition frequency	f _T	$V_{CE} = -6 \text{ V}, I_{C} = -20 \text{ mA}$	_	200	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = -6 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	13	_	pF

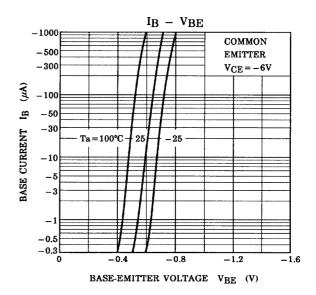
Note: h_{FE} (1) classification O: 70~140, Y: 120~240

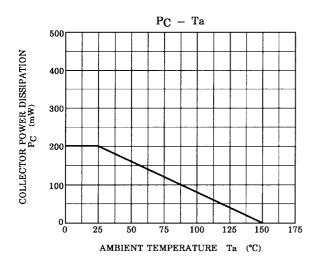
hFE (2) classification O: 25 (min), Y: 40 (min)











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